

<b>V<sub>DSS</sub> , -30V</b> <b>R<sub>DS(ON)</sub>, 4.3mΩ (max.) @ V<sub>GS</sub>=-10V</b> <b>R<sub>DS(ON)</sub>, 7.1mΩ (max.) @ V<sub>GS</sub>=-4.5V</b> <b>I<sub>D</sub> , -19A</b>	<b>PDFN 5x6-8L</b>		

Description	Features
<p>The SGP3003Q uses advanced trench technology MOSFETs to provide excellent R<sub>DS(ON)</sub> and low gate charge.</p> <p>The complementary Power MOSFETs may be used in H-bridge, Inverters and other applications.</p>	<ul style="list-style-type: none"> <li>• Low On-Resistance</li> <li>• Low Input Capacitance</li> <li>• Low Miller Charge</li> <li>• Low Input / Output Leakage</li> <li>• Pb-free lead plating; RoHS compliant</li> </ul>
	<b>Applications</b> <ul style="list-style-type: none"> <li>• Motor / Body Load Control</li> <li>• Automotive Systems</li> <li>• Load Switch</li> </ul>

## Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGP3003Q	Halogen-Free	PDFN 5x6-8L	Q	Tape & Reel	2,500

## Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Absolute Maximum Ratings (TA = 25 °C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	-30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current-Continuous	T <sub>A</sub> =25°C	I <sub>D</sub>	-25	A
	T <sub>A</sub> =75°C		-20	A
Drain Current-Pulsed <sup>Note 1</sup>		I <sub>DM</sub>	-100	A
Maximum Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	4.0	W
	T <sub>A</sub> =75°C		2.4	W
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range		T <sub>J</sub>	-55 to +150	°C

## Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Thermal resistance, Junction-to-Ambient <sup>Note 2</sup>	R <sub>θJA</sub>	Steady State	-	31.1	-	°C/W
Thermal resistance, Junction-to-Case	R <sub>θJC</sub>	Steady State	-	9.06	-	°C/W

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250μA	-1.2	-	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-18A	-	-	4.3	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>DS</sub> =-10A	-	-	7.1	mΩ
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	-	2.2	-	Ω

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1MHz	-	8433	-	pF
Output Capacitance	C <sub>oss</sub>		-	904	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	423	-	
Forward Transconductance	g <sub>fs</sub>	V <sub>D</sub> =-10V, I <sub>D</sub> =-5A	-	23	-	S

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω, I <sub>D</sub> =-1A	-	14.0	-	ns
Rise Time	t <sub>r</sub>		-	19.3	-	
Turn-Off Delay Time	T <sub>d(off)</sub>		-	196	-	
Fall Time	t <sub>f</sub>		-	58.6	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A	-	140	-	nC
Gate to Source Gate Charge	Q <sub>gs</sub>		-	27.1	-	
Gate to Drain "Miller" Charge	Q <sub>gd</sub>		-	18.3	-	

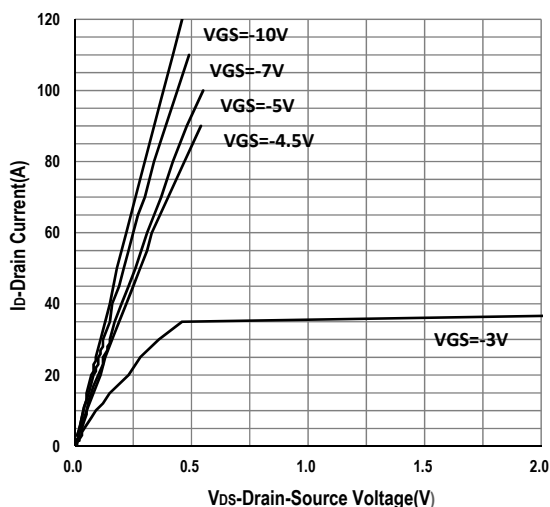
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A	-	-	-1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	V <sub>DD</sub> =-20V, I <sub>F</sub> =-18A, di/dt=100A/μs	-	33.8	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	28.9	-	nC

**Notes:**

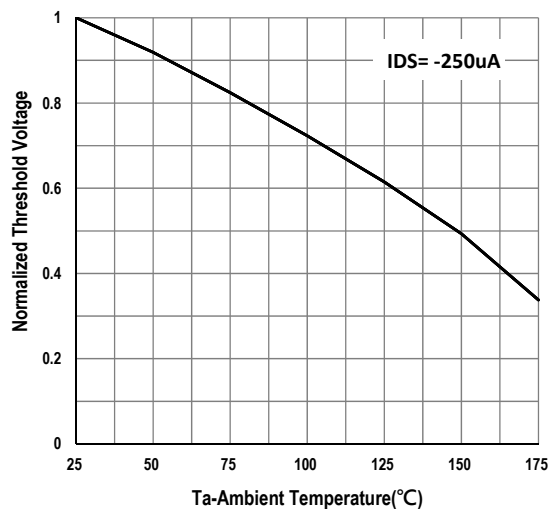
1. Pulse Test: Pulse Width ≤ 10ms, Duty Cycle ≤ 1%.
2. For surface-mounted devices, both R<sub>θJA</sub> and R<sub>θJC</sub> are measured with the device mounted on approximately 1"×1" FR-4 PCBs. In actual applications, many factors including the PCB material and layout, may affect the thermal resistance of the device-board assembly. For best results, characterize the thermal resistance directly in the application circuit.

## Typical Operating Characteristics

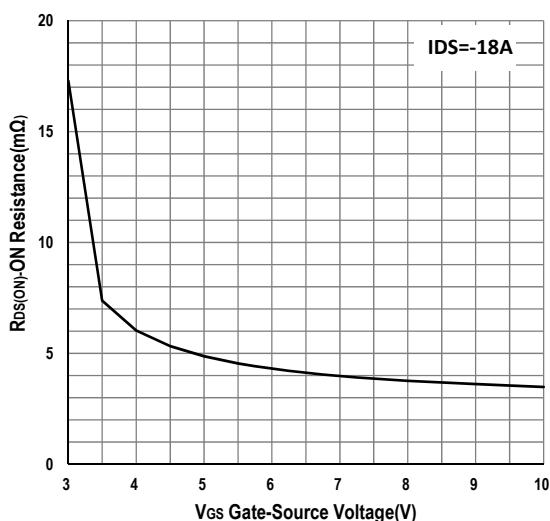
### Output Characteristics



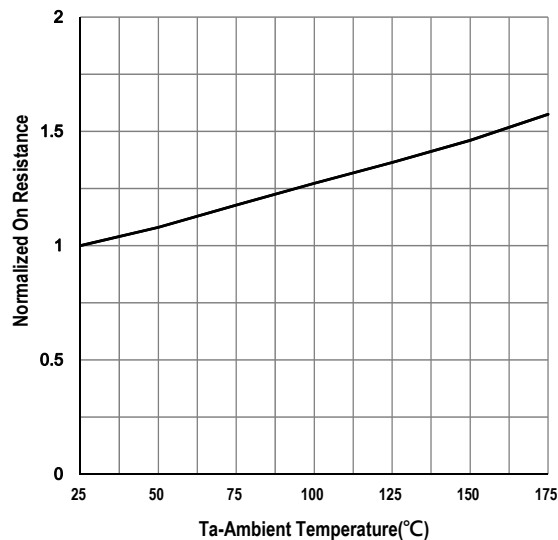
### Gate Threshold Voltage



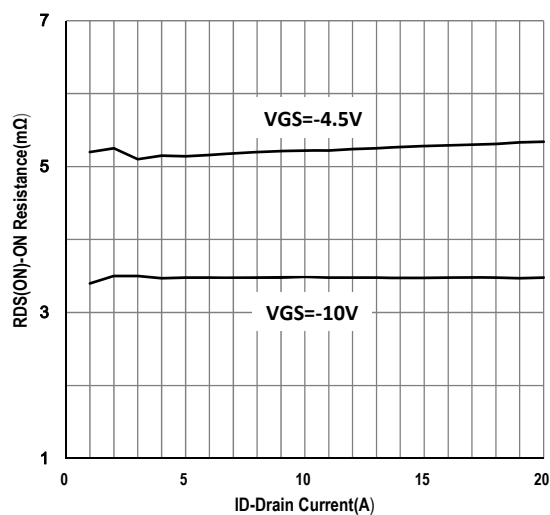
### Gate-Source On Resistance



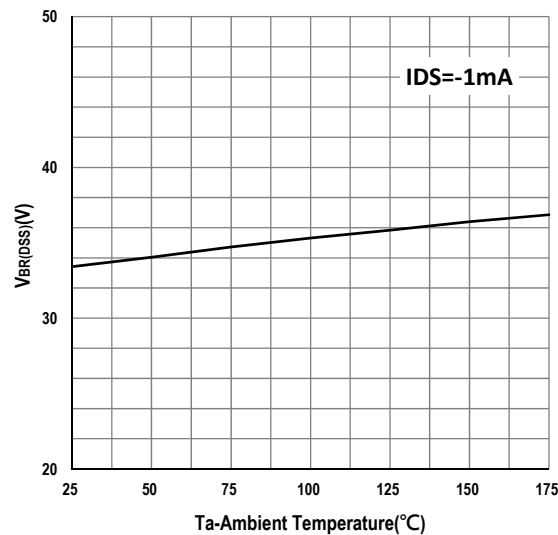
### Drain-Source On Resistance



### Drain-Source On Resistance

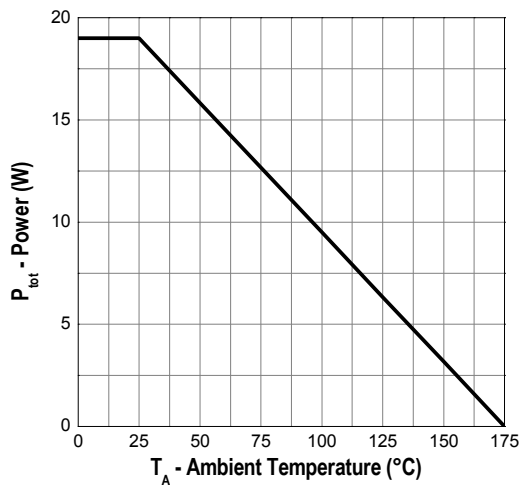


### Drain-source Breakdown Voltage

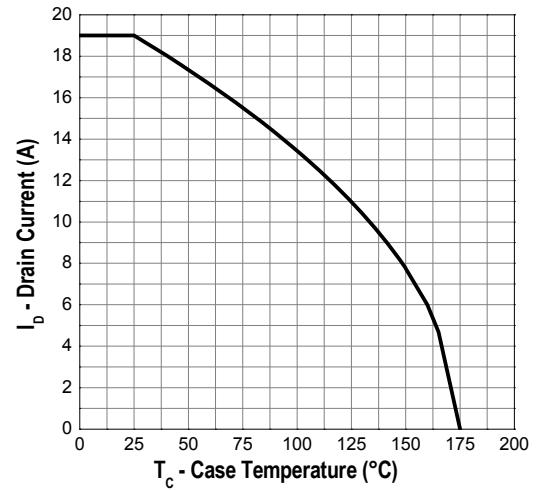


Typical Operating Characteristics (Cont.)

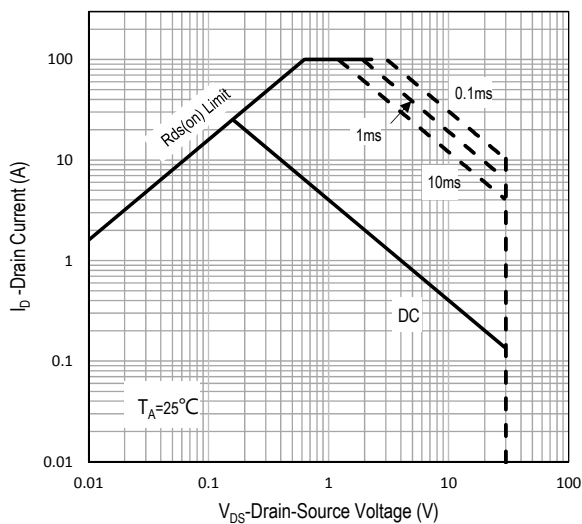
Power Dissipation



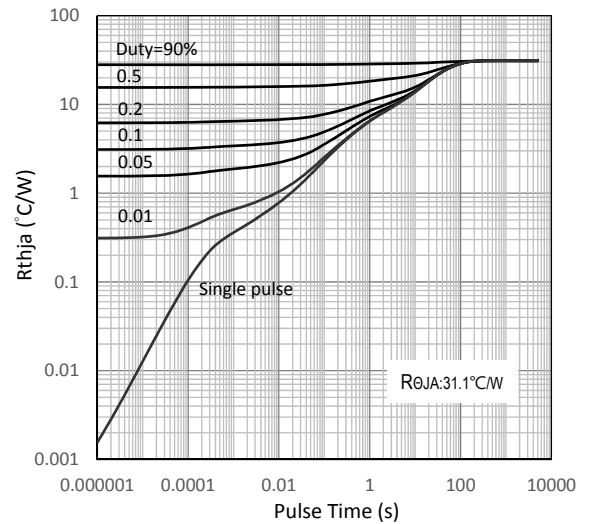
Drain Current



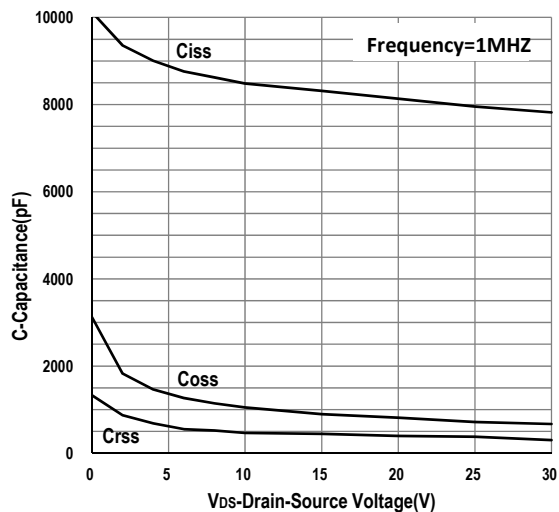
Safe Operation Area



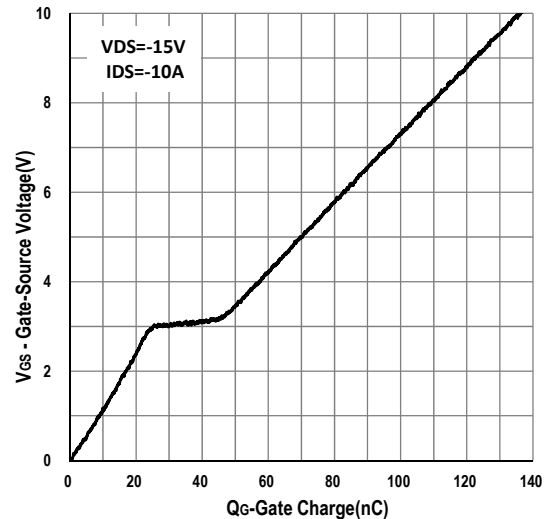
Transient Thermal Impedance



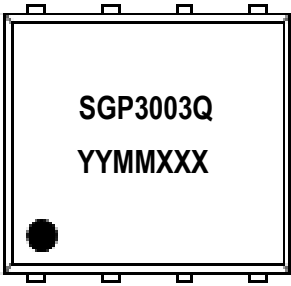
Capacitance



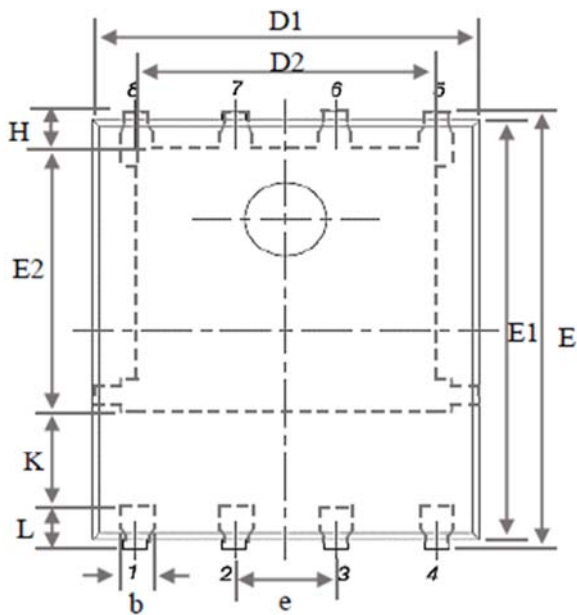
Gate Charge



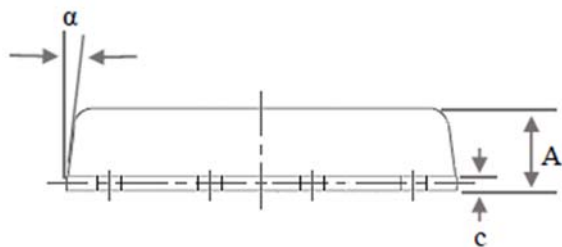
## Marking Information

PDFN 5x6-8L (Q)	Marking Rule
<p><a href="#">Laser Marking</a></p> 	<p><u>Line 1</u> : Device Name SGP3003Q</p> <p><u>Line 2</u> : Date Code YYMMXXX</p> <p>YY : Year Code MM : Month Code XXX : Serial Number</p>

**Package of Dimension**



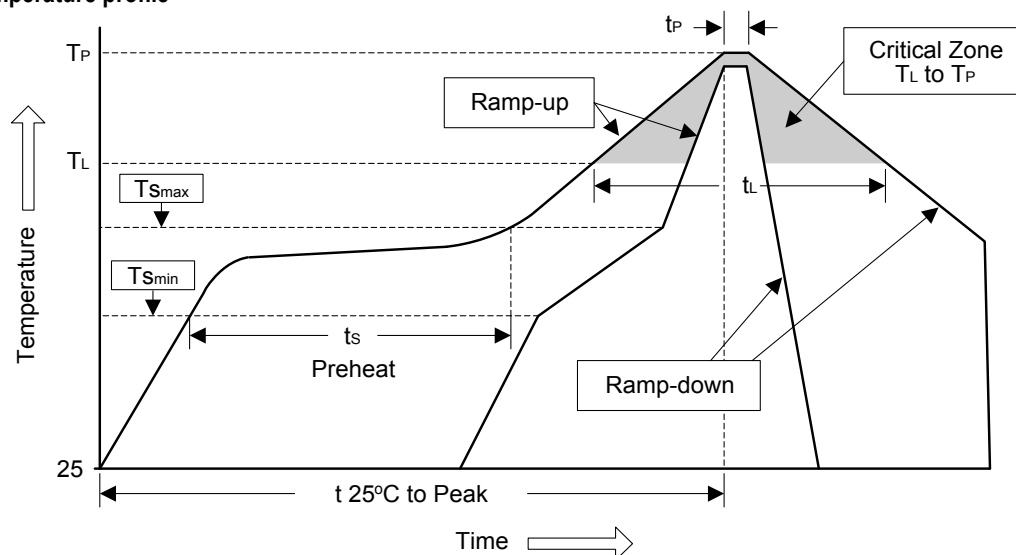
Symbol	Min	Nor	Max
A	0.90	1.04	1.17
b	0.33	0.42	0.51
C	0.06	0.20	0.35
D1	4.80	5.10	5.40
D2	3.61	3.96	4.31
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
e	1.27 BSC		
H	0.38	0.50	0.61
L	0.38	0.55	0.71
L1	0.05	0.15	0.25



## Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (TL to TP)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (TSmin)	100°C	150°C
- Temperature Max (TSmax)	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
TSmax to TL		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (TL)	183°C	217°C
- Time (tL)	60 to 150 sec	60 to 150 sec
Peak Temperature (TP)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (tP)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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